JJMICROELECTRONICS

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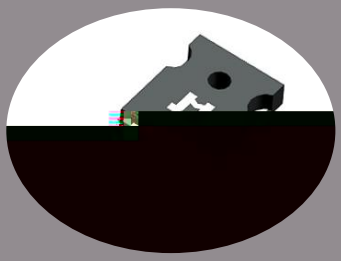
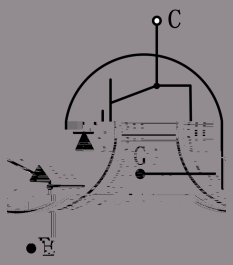
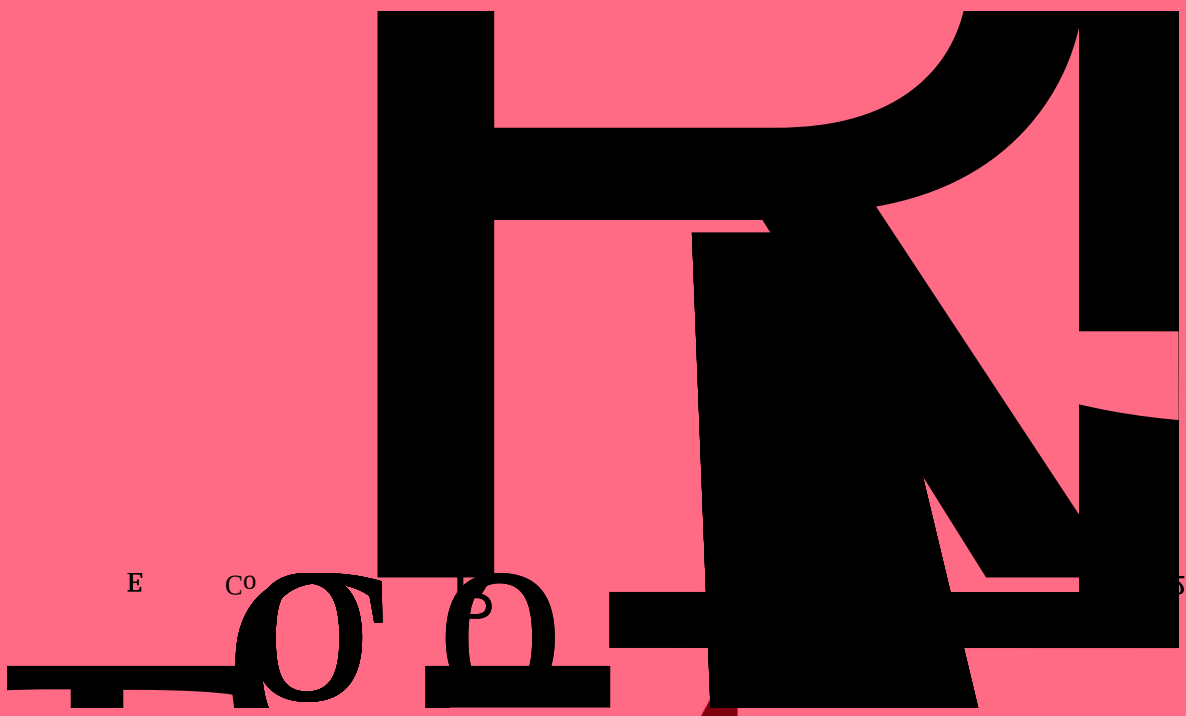




V_{CES}	Collector-emitter voltage	1200	V



E C0 [illegible] S

$_{CES}$	Collector-emitter breakdown voltage	$_{GE}$=0V, I_C=250μA	1200	-	-	V
$_{CES}$	Collector-emitter leakage current	$_{CE}$=1200V, $_{GE}$=0V	-	-	250	μA
	Gate leakage current, forward	$_{GE}$=20V, $_{CE}$=0V	-	-	100	nA
$_{GES}$	Gate leakage current, reverse	$_{GE}$=-20V, ? I'				

$t_{d(on)}$	Turn-on delay time		-	22	-	ns
t_r	Rise time		-	34	-	ns
$t_{d(off)}$	Turn-off delay time	V_{CC}=600V V_{GE}=0/15V	-	140	-	ns
t_f	Fall time	I_C=15A R_G=10	-	90	-	ns
E_{on}	Turn-on energy	Inductive load	-	0.9	-	mJ
E_{off}	Turn-off energy		-	0.7	-	mJ
E_{ts}	Total switching energy		-	1.6	-	mJ
$t_{d(on)}$	Turn-on delay time		-	22	-	ns
t_r	Rise time		-			
t_{rr}	Turning	V_{CC}=600V V_{GE}=0/15V I_C=15A R_G=10 Inductive load T_{vj} =175				

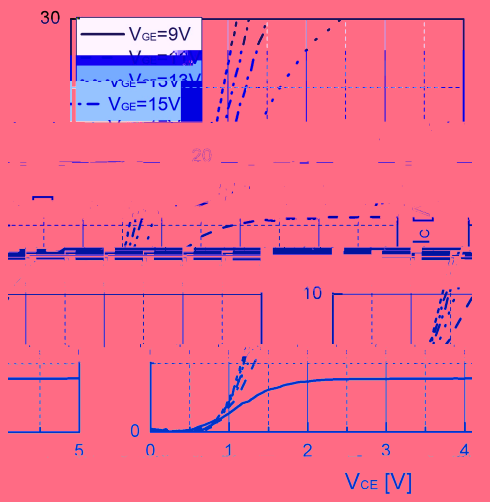


Fig 1. Typical output characteristic (vj=25)

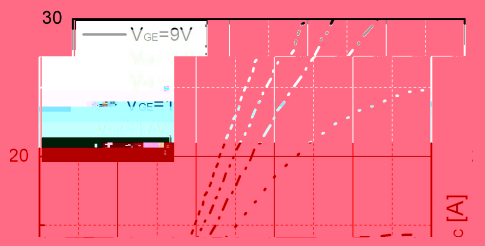


Fig 2. Typical output characteristic(vj=175)

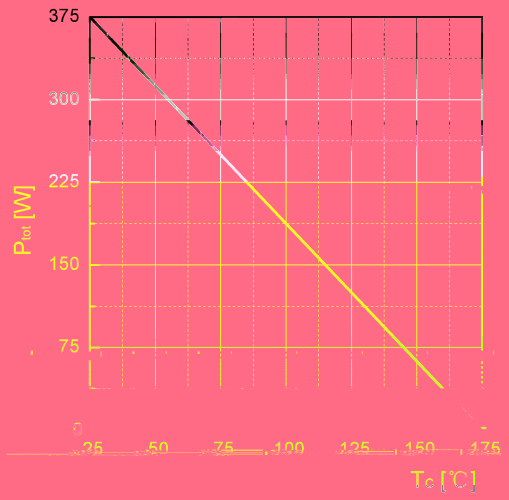


Fig 3. Power dissipation as a function of

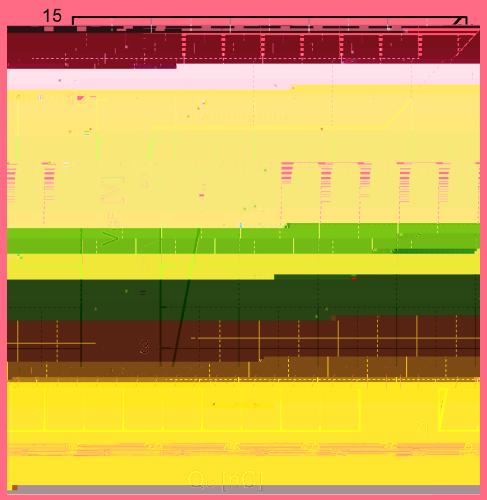


Fig 4. Typical Gate charge

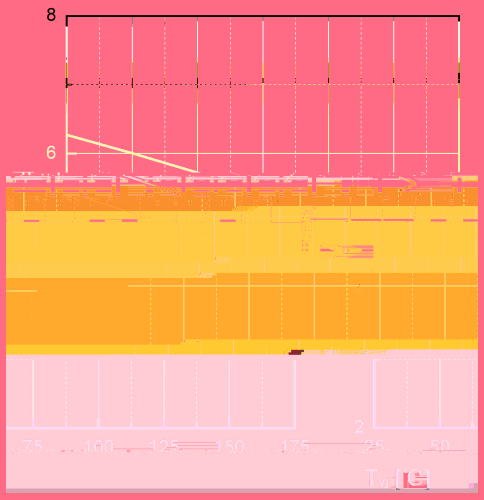


Fig 5. Typical GE(th) as a function of vj (C=1mA)

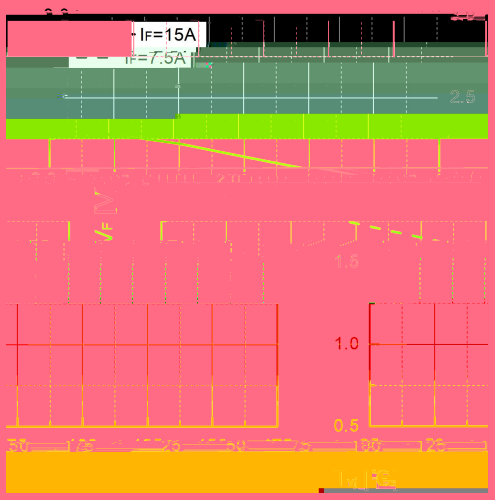


Fig 6. Typical F as a function of vj

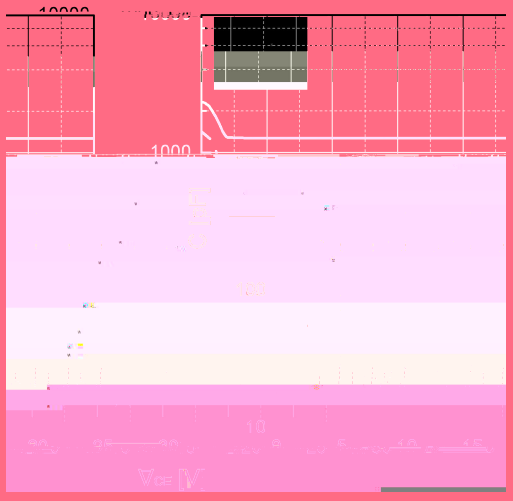


Fig 13. Typical capacitance as a function of $_{CE}$ (f=1Mhz, $_{GE}$=0V)

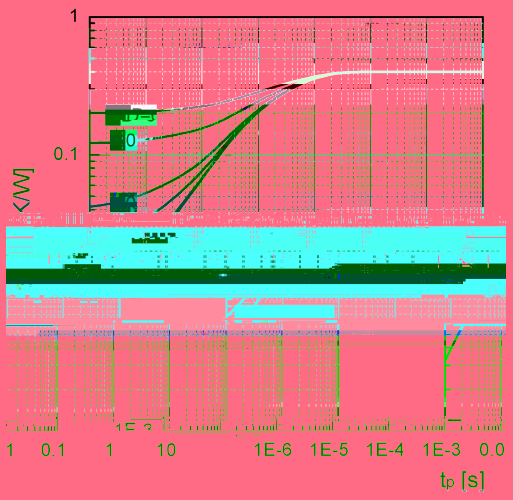


Fig 14. Transient thermal impedance of IGBT

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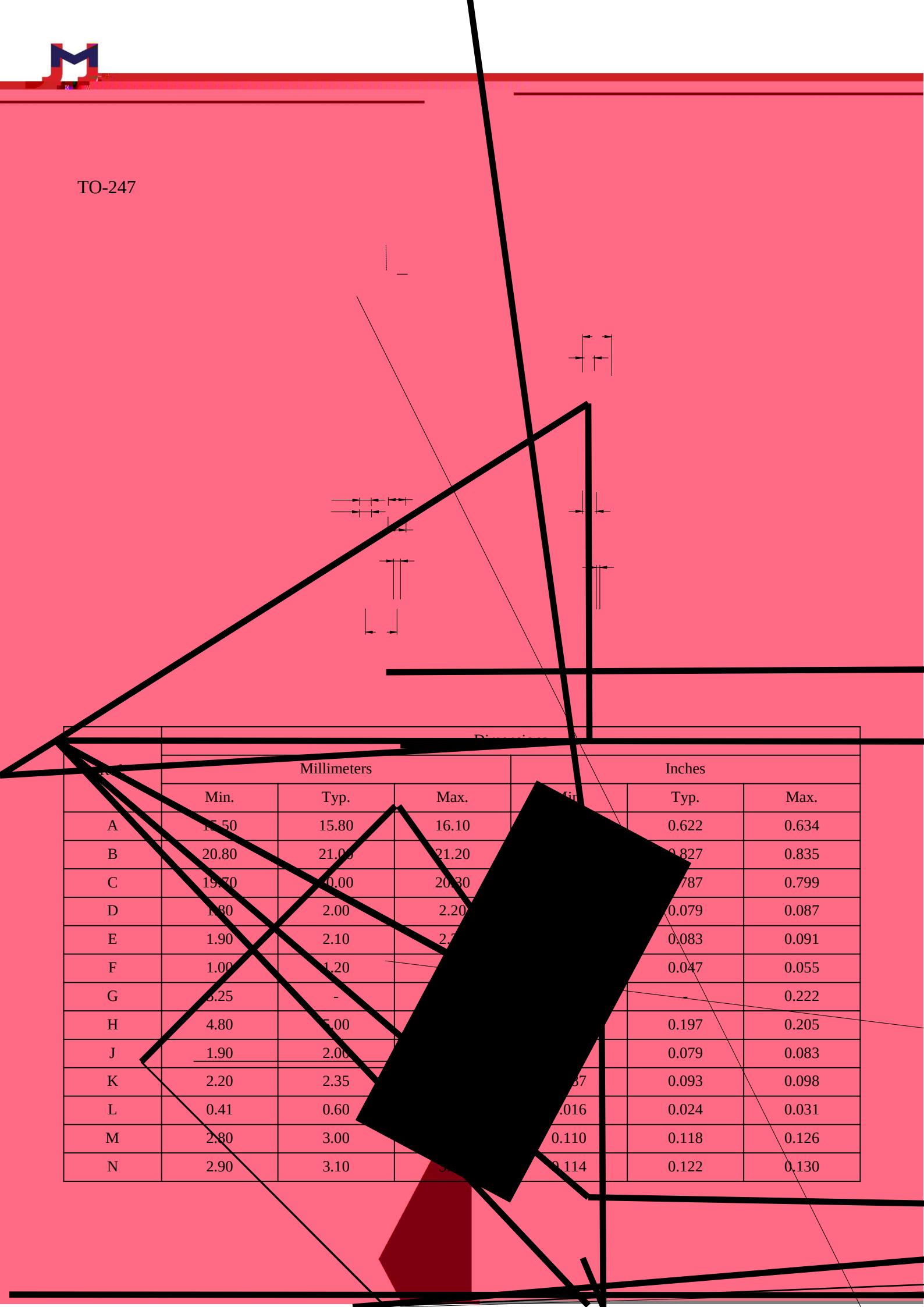

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.10		0.622	0.634
B	20.80	21.00	21.20		0.827	0.835
C	19.70	20.00	20.30		0.787	0.799
D	1.80	2.00	2.20		0.079	0.087
E	1.90	2.10	2.3		0.083	0.091
F	1.00	1.20			0.047	0.055
G	5.25	-			-	0.222
H	4.80	5.00			0.197	0.205
J	1.90	2.00			0.079	0.083
K	2.20	2.35		87	0.093	0.098
L	0.41	0.60		.016	0.024	0.031
M	2.80	3.00		0.110	0.118	0.126
N	2.90	3.10	3	0.114	0.122	0.130

Date	Revision	Changes
2023-12-12	Rev 1.0	Release of the datasheet
2024-03-20	Rev 1.1	Update
2024-05-17	Rev 1.2	Update